

IN THE CLAIMS

This is a complete and current listing of the claims, marked with status identifiers in parentheses. The following listing of claims will replace all prior versions and listings of claims in the application.

1. (Original) A semiconductor polishing composition comprising:

fumed silica, the semiconductor polishing composition being an aqueous dispersion solution of fumed silica,

wherein a content of the fumed silica having a particle diameter of 100 nm or less is 15% by volume or more based on a total amount of the fumed silica.

2. (Original) The semiconductor polishing composition of claim 1, wherein a content of fumed silica having a particle diameter of 100 nm or less is in a range of 15 to 90% by volume based on a total amount of the fumed silica.

3. (Currently Amended) The semiconductor polishing composition of claim 1--or--2, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 115 nm or less.

4. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 3~~, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

5. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 4~~, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

6. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 5~~, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

7. (Original) The semiconductor polishing composition of claim 6, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

8. (New) The semiconductor polishing composition of claim 2, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has

a particle size of the maximum frequency in a range of 115 nm or less.

9. (New) The semiconductor polishing composition of claim 2, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

10. (New) The semiconductor polishing composition of claim 3, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

11. (New) The semiconductor polishing composition of claim 8, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

12. (New) The semiconductor polishing composition of claim 2, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

13. (New) The semiconductor polishing composition of claim 3, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

14. (New) The semiconductor polishing composition of claim 4, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

15. (New) The semiconductor polishing composition of claim 2, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

16. (New) The semiconductor polishing composition of claim 3, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

17. (New) The semiconductor polishing composition of claim 4, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

18. (New) The semiconductor polishing composition of claim 5, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.